

SANYO	No.4234	2SJ263
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

Features

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.
- Micaless package facilitating mounting.

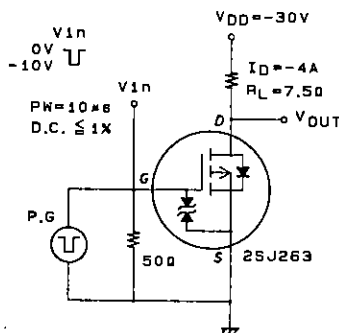
Absolute Maximum Ratings at Ta = 25°C

Drain to Source Voltage	V_{DS}		-60	V	
Gate to Source Voltage	V_{GS}		±15	V	
Drain Current(DC)	I_D		-6	A	
Drain Current(Pulse)	I_{DP}	$PW \leq 10\mu s, \text{ duty cycle} \leq 1\%$	-24	A	
Allowable Power Dissipation	P_D		2.0	W	
		$T_c = 25^\circ C$	25	W	
Channel Temperature	T_{ch}		150	°C	
Storage Temperature	T_{stg}		-55 to +150	°C	

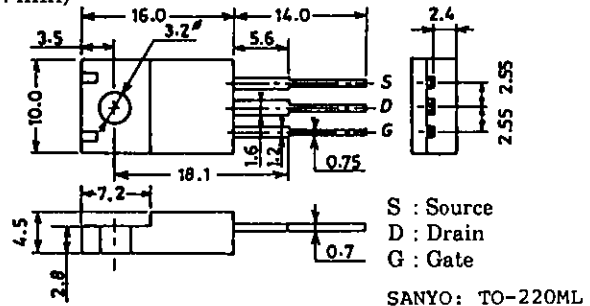
Electrical Characteristics at Ta = 25°C

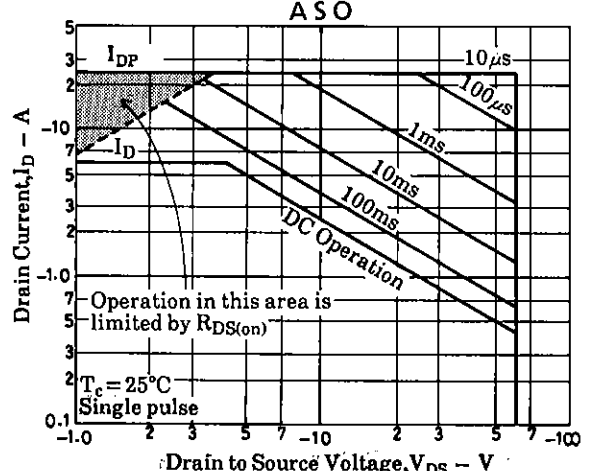
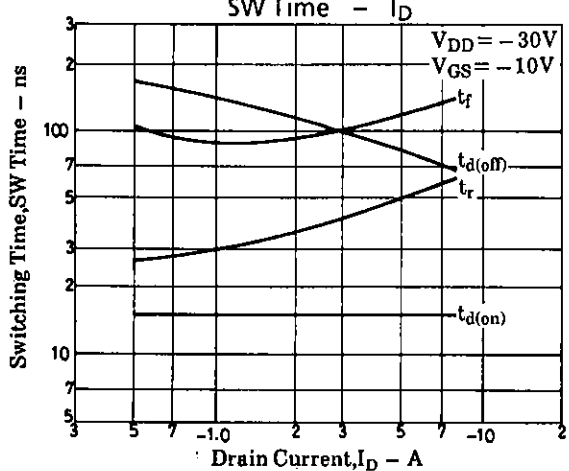
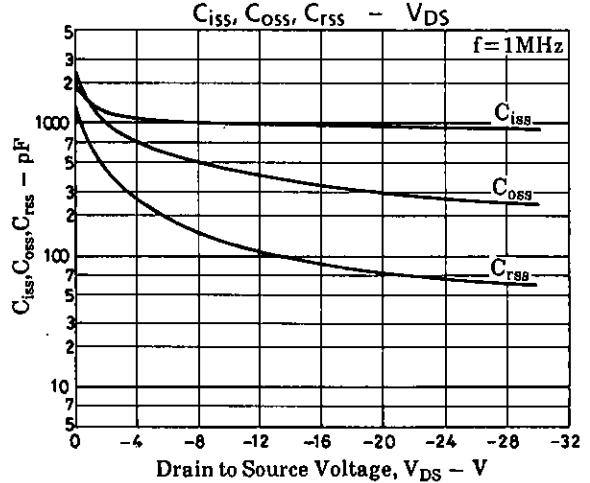
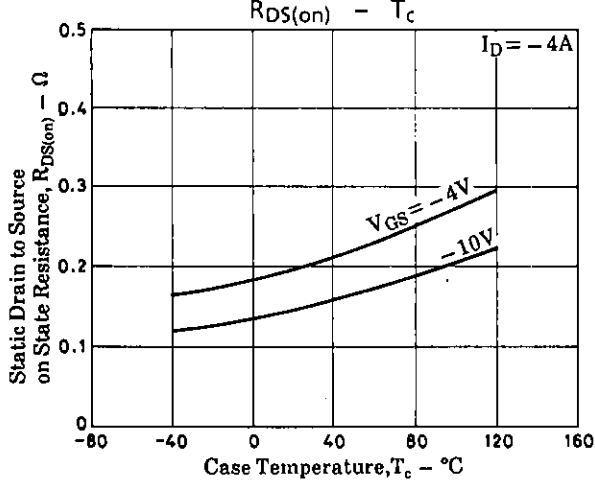
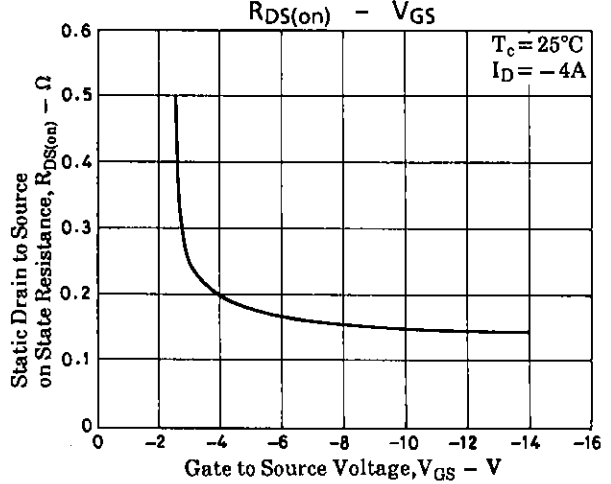
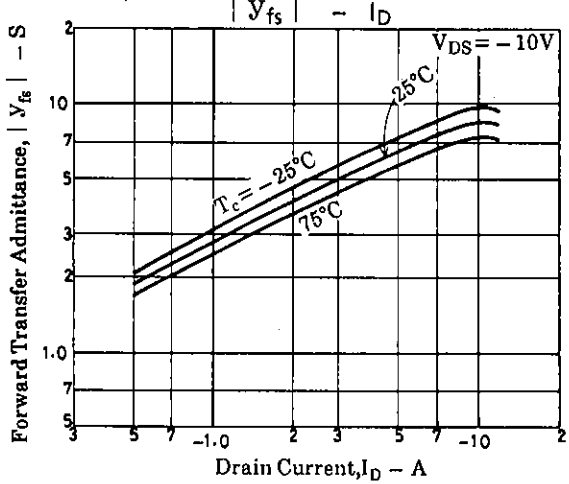
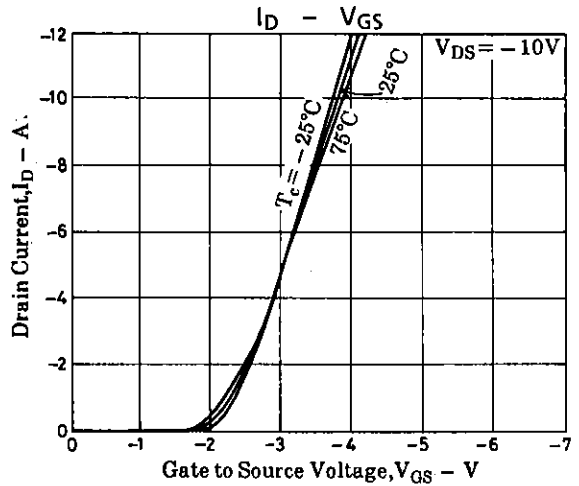
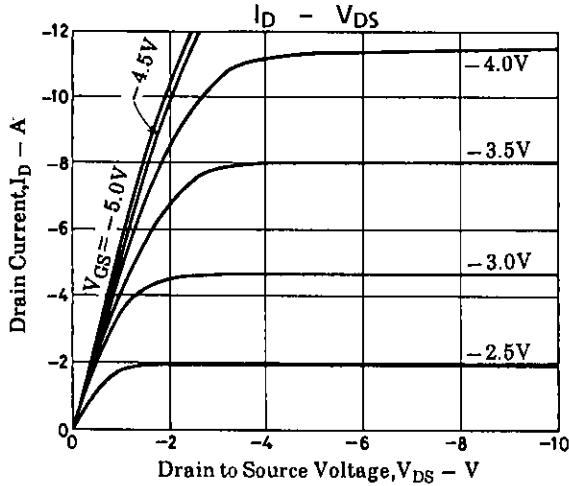
			min	typ	max	
D-S Breakdown Voltage	$V_{(BR)DSS}$	$I_D = -1mA, V_{GS} = 0$	-60			V
G-S Breakdown Voltage	$V_{(BR)GSS}$	$I_G = \pm 100\mu A, V_{DS} = 0$	±15			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -60V, V_{GS} = 0$			-100	μA
Gate to Source Leakage Current	I_{GSS}	$V_{GS} = \pm 12V, V_{DS} = 0$			±10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = -10V, I_D = -1mA$	-1.0		-2.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = -10V, I_D = -4A$	3.5	6		S
Static Drain to Source on State Resistance	$R_{DS(on)}$	$I_D = -4A, V_{GS} = -10V$		150	200	mΩ
	$R_{DS(on)}$	$I_D = -4A, V_{GS} = -4V$		200	270	mΩ
Input Capacitance	C_{iss}	$V_{DS} = -20V, f = 1MHz$		950		pF
Output Capacitance	C_{oss}	$V_{DS} = -20V, f = 1MHz$		300		pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = -20V, f = 1MHz$		75		pF
Turn-ON Delay Time	$t_{d(on)}$	See specified Test Circuit.		15		ns
Rise Time	t_r	"		45		ns
Turn-OFF Delay Time	$t_{d(off)}$	"		90		ns
Fall Time	t_f	"		110		ns
Diode Forward Voltage	V_{SD}	$I_S = -6A, V_{GS} = 0$	-1.0	-1.5		V

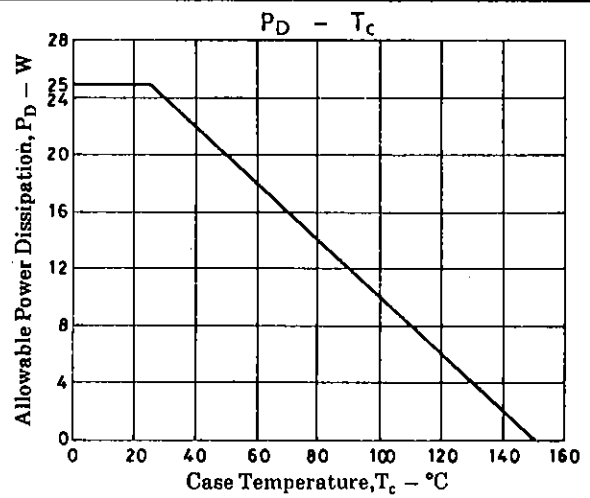
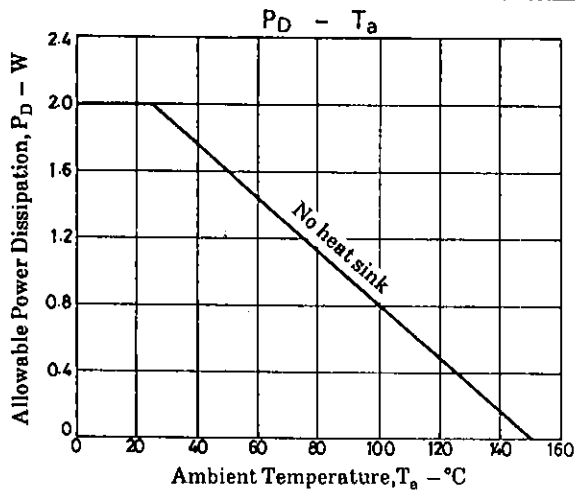
Switching Time Test Circuit



Package Dimensions 2063 (unit: mm)







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